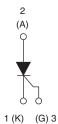


Vishay Semiconductors

### Phase Control SCR, 70 A





-247

PRODUCT SUMMARY						
Package	Super TO-247					
Diode variation	Single SCR					
I <sub>T(AV)</sub>	70 A					
$V_{DRM}$	1200 V, 1600 V					
$V_{TM}$	1.4 V					
I <sub>GT</sub>	100 A					
TJ	- 40 °C to 125 °C					

#### **FEATURES**

- High surge capability
- · High voltage input rectification
- Compliant to RoHS Directive 2002/95/EC
- Designed and qualified for industrial level



#### **APPLICATIONS**

- · AC switches
- High voltage input rectification (soft start)
- High current crow-bar
- Other phase-control circuits
- Designed to be used with Vishay input diodes, switches, and output rectifiers which are available in identical package outlines

#### **DESCRIPTION**

The VS-70TPS..PbF High Voltage Series of silicon controlled rectifiers are specifically designed for high and medium power switching, and phase control applications.

MAJOR RATINGS AND CHARACTERISTICS								
PARAMETER	TEST CONDITIONS	VALUES	UNITS					
I <sub>T(AV)</sub>	Sinusoidal waveform	70	Λ.					
I <sub>RMS</sub>	Lead current limitation	75	А					
$V_{RRM}/V_{DRM}$	Range	1200/1600	V					
I <sub>TSM</sub>		1400	А					
V <sub>T</sub>	100 A, T <sub>J</sub> = 25 °C	1.4	V					
dV/dt		500	V/µs					
dl/dt		150	A/µs					
T <sub>J</sub>		- 40 to 125	°C					

<b>VOLTAGE RATINGS</b>			
PART NUMBER	V <sub>RRM</sub> /V <sub>DRM</sub> , MAXIMUM REPETITIVE PEAK AND OFF-STATE VOLTAGE V	V <sub>RSM</sub> , MAXIMUM NON-REPETITIVE PEAK REVERSE VOLTAGE V	I <sub>RRM</sub> /I <sub>DRM</sub> AT 125 °C mA
VS-70TPS12PbF	1200	1300	15
VS-70TPS16PbF	1600	1700	15

<sup>\*</sup> Pb containing terminations are not RoHS compliant, exemptions may apply

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ABSOLUTE MAXIMUM RATINGS						
PARAMETER	SYMBOL	TEST CONDITIONS			VALUES	UNITS
Maximum average on-state current	I <sub>T(AV)</sub>	T <sub>C</sub> = 82 °C, 180° co	T <sub>C</sub> = 82 °C, 180° conduction half sine wave			
Maximum continuous RMS on-state current as AC switch	I <sub>T(RMS)</sub>	Lead current limitat	Lead current limitation			А
Maximum peak, one-cycle	I <sub>TSM</sub>	10 ms sine pulse, ra	ated V <sub>RRM</sub> applied		1200	
non-repetitive surge current	TSM	10 ms sine pulse, ne	o voltage reapplied	LOCAL T	1400	
Maximum I <sup>2</sup> t for fusing	l <sup>2</sup> t	10 ms sine pulse, ra	ated V <sub>RRM</sub> applied	Initial $T_J = T_J$ maximum	7200	A <sup>2</sup> s
Waximum 1-t for fusing	1-1	10 ms sine pulse, ne	10 ms sine pulse, no voltage reapplied		10 200	A-5
Maximum I <sup>2</sup> √t for fusing	I²√t	t = 0.1 ms to 10 ms,	102 000	A²√s		
Low level value of threshold voltage	V <sub>T(TO)1</sub>		0.916	V		
High level value of threshold voltage	V <sub>T(TO)2</sub>	T 405 00			1.21	V
Low level value of on-state slope resistance	r <sub>t1</sub>	T <sub>J</sub> = 125 °C			4.138	<b>~</b> 0
High level value of on-state slope resistance	r <sub>t2</sub>					mΩ
Maximum peak on-state voltage	$V_{TM}$	100 A, T <sub>J</sub> = 25 °C			1.4	V
Maximum rate of rise of turned-on current	dl/dt	T <sub>J</sub> = 25 °C			150	A/µs
Maximum holding current	I <sub>H</sub>				200	
Maximum latching current	ΙL	- T <sub>J</sub> = 25 °C			400	
Market and a second discrete and a second		T <sub>J</sub> = 25 °C			1.0	mA
Maximum reverse and direct leakage current	I <sub>RRM</sub> /I <sub>DRM</sub>	$T_J = 125 ^{\circ}\text{C}$ $V_R = \text{Rated } V_{RRM} / V_{DRM}$		15		
Maximum rate of rise of off-state voltage	dV/dt	T <sub>J</sub> = 125 °C			500	V/µs

TRIGGERING					
PARAMETER	SYMBOL		TEST CONDITIONS	VALUES	UNITS
Maximum peak gate power	$P_{GM}$	T = 30 µs		10	W
Maximum average gate power	P <sub>G(AV)</sub>	1 = 30 μs		2.5	\ \ \
Maximum peak gate current	I <sub>GM</sub>			2.5	Α
Maximum peak negative gate voltage	- V <sub>GM</sub>			10	
		T <sub>J</sub> = - 40 °C		4.0	v
Maximum required DC gate voltage to trigger	$V_{GT}$	T <sub>J</sub> = 25 °C	Anode supply = 6 V resistive load	1.5	ľ
		T <sub>J</sub> = 125 °C		1.1	
		T <sub>J</sub> = - 40 °C		270	
Maximum required DC gate current to trigger	$I_{GT}$	T <sub>J</sub> = 25 °C		100	mA
		T <sub>J</sub> = 125 °C		80	
Maximum DC gate voltage not to trigger	$V_{GD}$	T <sub>J</sub> = 120 °C, V <sub>DRM</sub> = Rated value		0.25	V
Maximum DC gate current not to trigger	$I_{GD}$			6	mA

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THERMAL AND MECH	ANICAL S	PECIFICA	TIONS		
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum junction temperature range		TJ		- 40 to 125	°C
Maximum storage temperature	range	T <sub>Stg</sub>		- 40 to 150	
Maximum thermal resistance, junction to case	,		DC operation	0.27	
Maximum thermal resistance, junction to ambient		R <sub>thJA</sub>		40	°C/W
Typical thermal resistance, case to heatsink		R <sub>thCS</sub>	Mounting surface, smooth and greased	0.2	
Approximate weight				6	g
				0.21	OZ.
Manusting to the second minimum				6 (5)	kgf · cm
Mounting torque	maximum			12 (10)	(lbf · in)
Marking device			Coop atula Super TO 247	70TPS	12
			Case style Super TO-247	70TPS	16

$\Delta R_{thJ-hs}$ Conduction per junction											
DEVICE	s	SINE HALF WAVE CONDUCTION REC						RECTANGULAR WAVE CONDUCTION			
DEVICE	180°	120°	90°	60°	30°	180°	120°	90°	60°	30°	UNITS
VS-70TPSPbF	0.078	0.092	0.117	0.172	0.302	0.053	0.092	0.125	0.180	0.306	°C/W

#### Note

• The table above shows the increment of thermal resistance R<sub>thJ-hs</sub> when devices operate at different conduction angles than DC

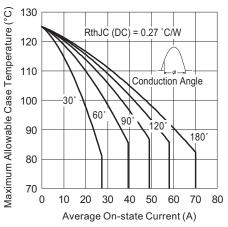


Fig. 1 - Current Rating Characteristics

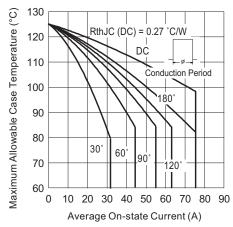


Fig. 2 - Current Rating Characteristics

## Vishay Semiconductors

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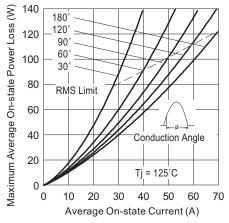


Fig. 3 - On-State Power Loss Characteristics

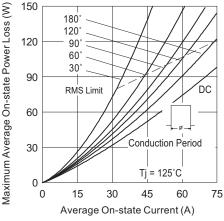


Fig. 4 - On-State Power Loss Characteristics

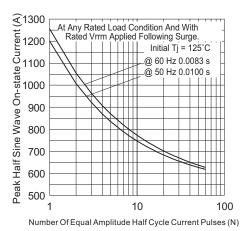


Fig. 5 - Maximum Non-Repetitive Surge Current

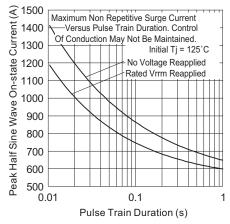


Fig. 6 - Maximum Non-Repetitive Surge Current

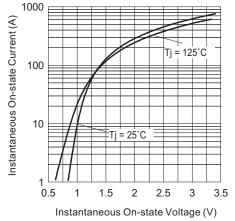


Fig. 7 - On-State Voltage Drop Characteristics

Phase Control SCR, 70 A

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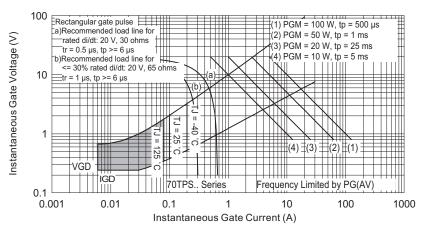


Fig. 8 - Gate Characteristics

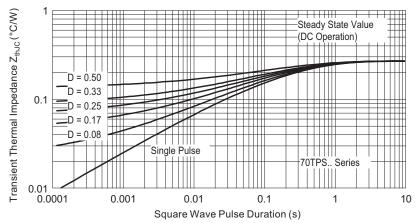


Fig. 9 - Thermal Impedance Z<sub>thJC</sub> Characteristics

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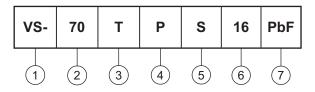


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#### **ORDERING INFORMATION TABLE**

**Device code** 



1 - Vishay Semiconductors product

2 - Current rating (70 = 70 A)

Circuit configuration:

T = Thyristor

4 - Package:

P = Super TO-247

5 - Type of silicon:

S = Standard recovery rectifier

12 = 1200 V 16 = 1600 V

- Voltage code x 100 = V<sub>RRM</sub>

• None = Standard production

• PbF = Lead (Pb)-free

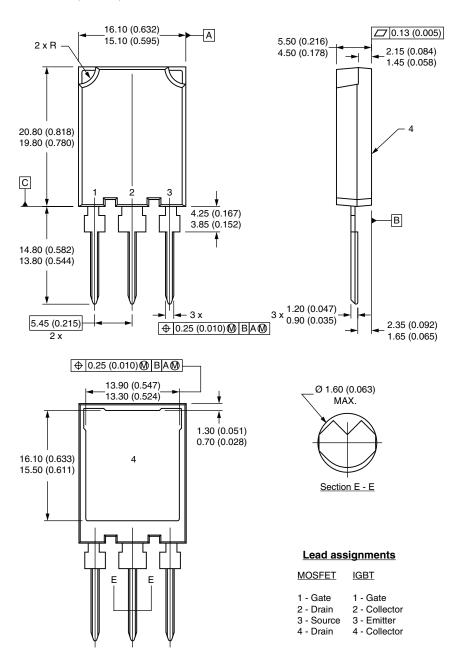
LINKS TO RELATED DOCUMENTS					
Dimensions www.vishay.com/doc?95073					
Part marking information <u>www.vishay.com/doc?95070</u>					



### Vishay High Power Products

## Super TO-247

#### **DIMENSIONS** in millimeters (inches)



#### Notes

- (1) Dimension and tolerancing per ASME Y14.5M-1994
- (2) Controlling dimension: millimeter
- (3) Outline conforms to JEDEC outline TO-274AA





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